

CMLD6263

**SURFACE MOUNT SILICON
DUAL, ISOLATED
HIGH VOLTAGE
SCHOTTKY DIODE**

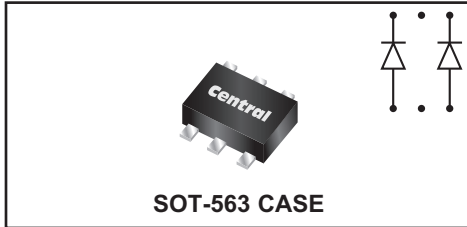


www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLD6263 incorporates two galvanically isolated, high voltage, low V_F silicon diodes in a space saving SOT-563 surface mount package. These diodes are designed for fast switching applications requiring a low forward voltage drop.

MARKING CODE: 63D or 63



SOT-563 CASE

FEATURES:

- High Voltage (70V)
- Low Forward Voltage
- Galvanically Isolated

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	70	V
Continuous Forward Current	I_F	15	mA
Peak Forward Surge Current, $t_p=1.0\text{s}$	I_{FSM}	50	mA
Power Dissipation	P_D	250	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	500	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=50\text{V}$		98	200	nA
BV_R	$I_R=10\mu\text{A}$	70			V
V_F	$I_F=1.0\text{mA}$		395	410	mV
C_J	$V_R=0, f=1.0\text{MHz}$			2.0	pF
t_{rr}	$I_R=I_F=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

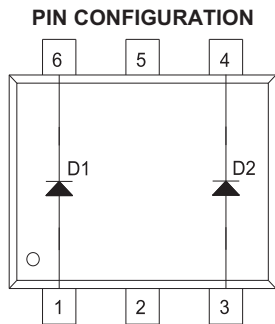
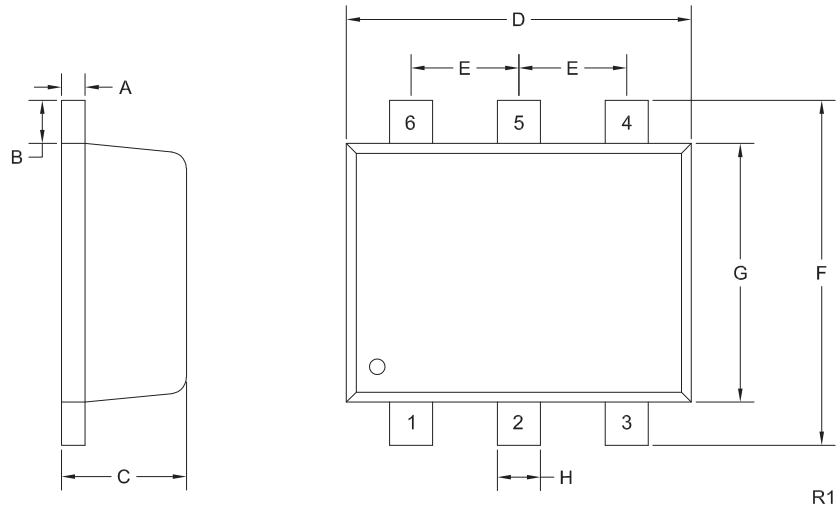
R5 (15-September 2014)

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SOT-563 CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.0027	0.007	0.07	0.18
B	0.008		0.20	
C	0.017	0.024	0.45	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.045	0.049	1.15	1.25
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R1)

LEAD CODE:

- 1) Anode D1
- 2) NC
- 3) Anode D2
- 4) Cathode D2
- 5) NC
- 6) Cathode D1

MARKING CODE: 63D or 63

R5 (15-September 2014)